Determination of Ultra Trace Elements in High Purity Reagents by Automatic Standard Addition Methods Using prepFASTS - ICP-MS/MS.

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# Introduction

- Ultratrace analysis at the pg/g (ppt) or fg/g (ppq) level using a highly sensitive instrument such as ICP-MS is susceptible to contamination from the lab environment or reagents.
- Given the challenging nature of the (SEMI) publishes standard specifications for semiconductor process chemicals, including H<sub>2</sub>O<sub>2</sub> (SEMI C30-1110 - Specifications for Hydrogen Peroxide) [1].
- SEMI Grade 5 is the highest purity level, with maximum contamination levels of 10 ppt for most trace elements.
- SEMI Standard C30-1110 specifies the maximum concentration of sulfate and phosphate allowed in high purity  $H_2O_2$ , with a limit of 30,000 ppt. This equates to an elemental concentration of sulfur (S) and phosphorus (P) of 10,000 ppt.
- Currently, ICP-QMS isn't used to measure these two elements, but triple quadrupole ICP-MS (ICP-MS/MS or ICP-QQQ) permits much lower limits of detection for S and P.
- The development of ICP-MS/MS means all SEMI specified elements can now be monitored using a single technique [2].

In this study, impurities in deionized water (DIW) and  $H_2O_2$  were quantified by automatic Method of Standard Addition (MSA) using a prepFAST S (Elemental Scientific, USA) and Agilent 8900 ICP-MS/MS (Agilent Technologies, USA). The method allows the quantification of ultra-trace level impurities in  $H_2O_2$  and DIW regardless of the skill level of the analyst.

### **Experimental**

#### Reagents and sample

### **Results and Discussion**





Figure 3. MSA calibration curves.

Table 4. DLs and BECs in DIW and  $H_2O_2$ . Analytes shown in bold are SEMIC30-1110 Grade 5 elements.

- TAMAPURE-AA-10 hydrogen peroxide (35% H<sub>2</sub>O<sub>2</sub>, Tama Chemicals, Japan) and DIW (Milli-Q water, Molsheim, France) were used as the samples.
- Standard stock solution for MSA: a 1000 ppt mixed multi-element standard solution was prepared by diluting a 10 ppm mixed multi-element standard solution (SPEX CertiPrep, NJ, US) with 1% HNO<sub>3</sub>.
- Standard stock solution for acid spiking (10%): a 10% nitric acid solution was prepared by diluting 68% ultrapure HNO<sub>3</sub> (TAMAPURE-AA-10) with DIW. HNO<sub>3</sub> was used to stabilize the spiked elements in the  $H_2O_2$  sample.
- The two stock solutions were loaded on the *prepFAST* S autosampler.
- All target concentration solutions required for the analysis were automatically prepared by the prepFAST S system.
- All preparation and analysis steps were performed in a Class 10,000 clean room.

#### Instrumentation

- A standard Agilent 8900 Semiconductor configuration ICP-QQQ instrument was equipped with a PFA coaxial nebulizer that is included with the prepFAST S system. This configuration of ICP-QQQ is fitted with a Peltier cooled quartz spray chamber, quartz torch (2.5 mm id), platinum-tipped sampling and skimmer cones, and s-lens.
- The 8900 ICP-QQQ was connected to the ESI automated sample preparation and injection system. Instrument operating conditions are given in Tables 1,2 and 3. And Figure 1 shows an illustration of the prepFAST S.

#### Table 1. ICP-MS/MS operating conditions.

	Cool no gas	Cool NH₃	Cool NH₃ soft	No gas	H <sub>2</sub>	He	02	Soft O <sub>2</sub>
Scan type	Single MS/MS							
RF power (W)	600			1500				
Sample Depth (mm)	18			8				
Carrier gas flow rate	$\cap$ 7							
(L/min)				0.7				
Makeup gas flow rate (L/min)	0.9			0.48				
Extract 1 (V)	-15	50	-100	4.2	4.7	4.2	4.5	3.5
Extract 2 (V)	-18	-17	-12	-250				120
Omega bias (V)	-70			-140 -70				-70
Omega lens (V)	2.0			10.0	8.0	10.0	10.5	4.0
Q1 entrance (V)	-15		-50					
He gas flow rate (mL/min)	_		1	_	_	5	_	_
H <sub>2</sub> gas flow rate (mL/min)	_	_	_	-	7	_	-	_
NH <sub>3</sub> gas flow rate (mL/min)	_	3		_	-	_	_	_
O <sub>2</sub> gas flow rate (mL/min)			_	-	-	-		4.5
OctP bias (V)	-20	-10		-8 -18			-3	
Axial Acceleration (V)	0	1.5		0			1	
Energy discrimination (V)	15	-5		5	0	3	-7	

Table 3. prepFAST S operating conditions.

	DIW	$H_2O_2$		
Carrier flow rate (µL/min)	100			
Dilution factor	1 (no-dilution)			
Stock standard conc. (ng/L)	1000 (1.0 % HNO <sub>3</sub> )			
Conc. of HNO <sub>3</sub> used for spike (%)	-	10		
Conc. of $HNO_3$ in the sample after acid spiking (%)	0	0.5		

**Electronics in Rear Plenum** UPW Polishing Columns UPW is used as carrier, diluent 

				DIW		$H_2O_2$		
	Q1	Q2	Tune Mode	conc.	D.L.	conc.	D.L.	
				ng/L	ng/L	ng/L	ng/L	
Li		7	Cool no gas	< D.L.	0.003	< D.L.	0.025	
Be	9	9	No Gas	< D.L.	0.096	< D.L.	0.089	
В	11	11	No Gas	1.7	0.52	22	1.9	
Na		23	Cool no gas	0.35	0.077	1.1	0.11	
Mg		24	Cool no gas	< D.L.	0.015	0.053	0.040	
Al		27	Cool no gas	< D.L.	0.040	0.63	0.22	
Si	28	28	H <sub>2</sub>	85	3.8	500	26	
Ρ	31	47	O <sub>2</sub>	10	4.4	9.4	2.6	
S	32	48	O <sub>2</sub>	120	2.3	220	7.5	
K	39	39	Cool NH3 soft	0.13	0.049	0.45	0.19	
Ca	40	40	Cool NH3 soft	< D.L.	0.082	0.67	0.60	
Ti	48	64	soft O <sub>2</sub>	< D.L.	0.042	< D.L.	0.24	
V	51	67	soft O <sub>2</sub>	0.026	0.021	0.068	0.058	
Cr	52	52	Cool NH <sub>3</sub>	< D.L.	0.085	0.69	0.24	
Mn	55	55	Cool NH <sub>3</sub>	0.010	0.010	< D.L.	0.039	
Fe	56	56	Cool NH <sub>3</sub>	0.076	0.070	< D.L.	0.29	
Со	59	59	Cool NH <sub>3</sub>	< D.L.	0.017	< D.L.	0.025	
Ni	60	60	Cool NH <sub>3</sub>	< D.L.	0.080	< D.L.	0.24	
Cu	63	63	Cool NH <sub>3</sub>	< D.L.	0.12	< D.L.	0.17	
Zn	64	64	He	0.28	0.063	0.47	0.41	
Ga		71	Cool no gas	< D.L.	0.011	< D.L.	0.032	
Ge	74	74	He	< D.L.	0.36	< D.L.	0.27	
As	75	91	soft O <sub>2</sub>	< D.L.	0.072	< D.L.	0.15	
Se	78	78	H <sub>2</sub>	< D.L.	0.20	< D.L.	0.40	
Rb		85	Cool no gas	< D.L.	0.031	< D.L.	0.052	
Sr	88	88	He	< D.L.	0.024	0.000*	0.000*	
Nb	93	93	He	< D.L.	0.018	< D.L.	0.030	
Mo	98	98	He	< D.L.	0.093	< D.L.	0.065	
Ru	101	101	He	< D.L.	0.077	< D.L.	0.075	
Rh	103	103	soft O <sub>2</sub>	0.10	0.057	0.097	0.018	
Pd	105	105	No Gas	0.12	0.078	0.090	0.055	
Ag	107	107	No Gas	0.14	0.099	< D.L.	0.031	
Cd	114	114	No Gas	< D.L.	0.045	< D.L.	0.047	
In	115	115	No Gas	< D.L.	0.009	< D.L.	0.022	
Sn	118	118	No Gas	0.059	0.038	< D.L.	0.20	
Sb	121	121	H <sub>2</sub>	0.032	0.029	< D.L.	0.028	
Те	125	125	No Gas	< D.L.	0.18	0.000^	0.000^	
Cs		133	Cool no gas	< D.L.	0.074	< D.L.	0.088	
Ba	138	138	H <sub>2</sub>	< D.L.	0.023	< D.L.	0.039	
Та	181	181	No Gas	0.041	0.024	0.28	0.12	
W	182	182	No Gas	< D.L.	0.037	0.044	0.044	
Re	185	185	No Gas	< D.L.	0.040	< D.L.	0.062	
lr	193	193	No Gas	< D.L.	0.023	< D.L.	0.040	
Pt	195	195	H <sub>2</sub>	0.33	0.28	0.39	0.088	
Au	197	197	No Gas	< D.L.	0.051	< D.L.	0.22	
	205	205	No Gas	0.082	0.036	< D.L.	0.015	
Pb	208	208	No Gas	0.066	0.042	< D.L.	0.056	
Bi	209	209	No Gas	0.048	0.034	0.054	0.027	
U	238	238	No Gas	< D.L.	0.004	< D.L.	0.012	

#### Table 2. Acquisition parameters.

Parameter	Setting			
Q2 peak pattern	1 point			
Replicates	3 (spiked solution) 10 (unspiked solution)			
Sweeps/Replicate	10			
Integration time	1 s for all isotopes			



Figure 1. prepFAST S system.

#### ESI prepFAST S operation

The prepFAST S combines an autosampler with a system of ultrapure valves (S1 -S5), and a set of high precision syringe pumps. Undiluted chemicals can be placed on the autosampler and the system will perform the actions required to prepare the sample for injection to the ICP-MS or ICP-QQQ. The operation of the prepFAST S is outlined in the four schematics shown in Figure 2.

1. Loading of sample: syringe S5 loads a precise amount of sample to the loop.



2. Sample dilution and sample spiking: syringes S1, S2, S3, and S4 mix the acid, sample, diluent, and spike solution.



DLs were calculated as 3-sigma of 10 replicate measurements of unspiked samples.

\*DLs and BECs for Sr and Te could not be calculated, as the background signal mean and SD were 0 counts per second.

# Conclusions

3. Sample injection: the prepared sample is introduced into the ICP-QQQ via S2. S2 provides a precise flow rate regardless of sample type.



4. Valve wash: deionized water (DIW) is used to clean the lines between S1 and S4 valves.



Figure 2. ESIprepFAST S system schematic, illustrating four distinct steps: sample loading during spray chamber rinse, sample preparation, injection, and cleaning.

- By providing a high degree of automation, the Agilent 8900 ICP-QQQ fitted with ESI's prepFAST S autodilution system simplifies the elemental analysis of DIW and 35%  $H_2O_2$ .
- Once the multielement standards, acid used for spiking, and samples have been loaded into the prepFAST S autosampler, the system performs all required steps including introduction of the sample to the ICP-QQQ.
- Automating the sample handling steps speeds up the analytical procedure and is easier for the analyst to perform. Eliminating manual tasks during ultratrace analysis lowers the risk of contamination. It also reduces the likelihood of errors arising during the experimental procedure, leading to an increased confidence in the data quality.
- All the elements specified in SEMI C30-1110, including P and S (and many other elements), were measured at sub-ppt to ppt levels in DIW and high purity 35%  $H_2O_2$ . The results exceeded current SEMI specifications for  $H_2O_2$ .

### Referencess

- SEMI C30-1110, Specifications for hydrogen peroxide (2010).
- Kazuo Yamanaka, Determination of ultra trace elements in high purity hydrogen peroxide with Agilent 8900 ICP-QQQ, Agilent publication (2016), 5991-7701EN.